

Medium Power Phase Control Thyristors (Stud Version), 25 A



TO-208AA (TO-48)

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High di/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

PRODUCT SUMMARY	
Package	TO-208AA (TO-48)
Diode variation	Single SCR
$I_{T(AV)}$	25 A
V_{DRM}/V_{RRM}	100 V to 1200 V
V_{TM}	1.70 V
I_{GT}	60 mA
T_J	-65 °C to 125 °C

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		25	A
	T_C	85	°C
$I_{T(RMS)}$		40	A
I_{TSM}	50 Hz	420	A
	60 Hz	440	
I^2t	50 Hz	867	A ² s
	60 Hz	790	
V_{DRM}/V_{RRM}		100 to 1200	V
t_q	Typical	110	µs
T_J		-65 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-25RIA	10	100	150	20
	20	200	300	10
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if di/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \leq 5$ ms



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° sinusoidal conduction			25	A
					85	°C
Maximum RMS on-state current	I _{T(RMS)}				40	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	420	A
		t = 8.3 ms			440	
		t = 10 ms	100 % V _{RRM} reapplied		350	
		t = 8.3 ms			370	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		867	A ² s
		t = 8.3 ms			790	
		t = 10 ms	100 % V _{RRM} reapplied		615	
		t = 8.3 ms			560	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum			8670	A ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			0.99	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.40	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			10.1	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			5.7	
Maximum on-state voltage	V _{TM}	I _{pk} = 79 A, T _J = 25 °C			1.70	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 6 V, resistive load			130	mA
Latching current	I _L				200	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum rate of rise of turned-on current	$V_{\text{DRM}} \leq 600 \text{ V}$	dI/dt	$T_J = T_J$ maximum, $V_{\text{DM}} = \text{Rated } V_{\text{DRM}}$ Gate pulse = 20 V, 15 Ω , $t_p = 6 \text{ }\mu\text{s}$, $t_r = 0.1 \text{ }\mu\text{s}$ maximum $I_{\text{TM}} = (2 \times \text{rated } dI/dt) \text{ A}$	200	A/ μs
	$V_{\text{DRM}} \leq 800 \text{ V}$			180	
	$V_{\text{DRM}} \leq 1000 \text{ V}$			160	
	$V_{\text{DRM}} \leq 1600 \text{ V}$			150	
Typical turn-on time		t_{gt}	$T_J = 25 \text{ }^\circ\text{C}$, at rated $V_{\text{DRM}}/V_{\text{RRM}}$, $T_J = 125 \text{ }^\circ\text{C}$	0.9	μs
Typical reverse recovery time		t_{rr}	$T_J = T_J$ maximum, $I_{\text{TM}} = I_{\text{T(AV)}}$, $t_p > 200 \text{ }\mu\text{s}$, $dI/dt = -10 \text{ A}/\mu\text{s}$	4	
Typical turn-off time		t_{q}	$T_J = T_J$ maximum, $I_{\text{TM}} = I_{\text{T(AV)}}$, $t_p > 200 \text{ }\mu\text{s}$, $V_R = 100 \text{ V}$, $dI/dt = -10 \text{ A}/\mu\text{s}$, $dV/dt = 20 \text{ V}/\mu\text{s}$ linear to 67 % V_{DRM} , gate bias 0 V to 100 W	110	

Note

- $t_q = 10$ μs up to 600 V, $t_q = 30$ μs up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/ μs
		$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	300 ⁽¹⁾	

Note

- ⁽¹⁾ Available with: $dV/dt = 1000$ V/ μs , to complete code add S90 i.e. 25RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}	T _J = T _J maximum		8.0	W
Maximum average gate power	P _{G(AV)}			2.0	
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum		1.5	A
Maximum peak negative gate voltage	-V _{GM}	T _J = T _J maximum		10	V
DC gate current required to trigger	I _{GT}	T _J = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
		T _J = 25 °C		60	
		T _J = 125 °C		35	
DC gate voltage required to trigger	V _{GT}	T _J = - 65 °C		3.0	V
		T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction and storage temperature range	T _J , T _{Stg}		- 65 to 125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.75	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.35	
Allowable mounting torque		Non-lubricated threads	3.4 + 0 - 10 % (30)	N · m (lbf · in)
		Lubricated threads	23 + 0 - 10 % (20)	
Approximate weight			14	g
			0.49	oz.
Case style		See dimensions - link at the end of datasheet	TO-208AA (TO-48)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13	$T_J = T_J$ maximum	K/W
120°	0.21	0.22		
90°	0.27	0.30		
60°	0.40	0.42		
30°	0.69	0.70		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

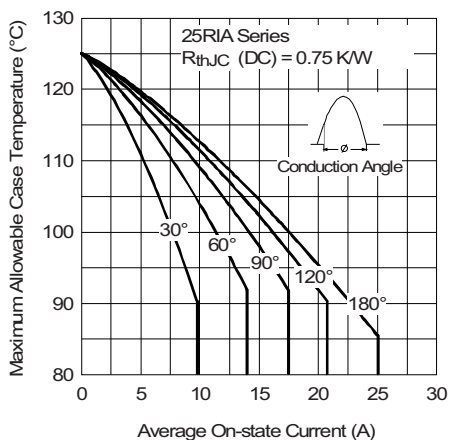


Fig. 1 - Current Ratings Characteristics

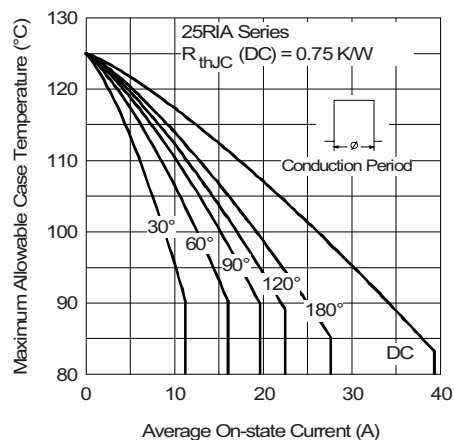


Fig. 1 - Current Ratings Characteristics

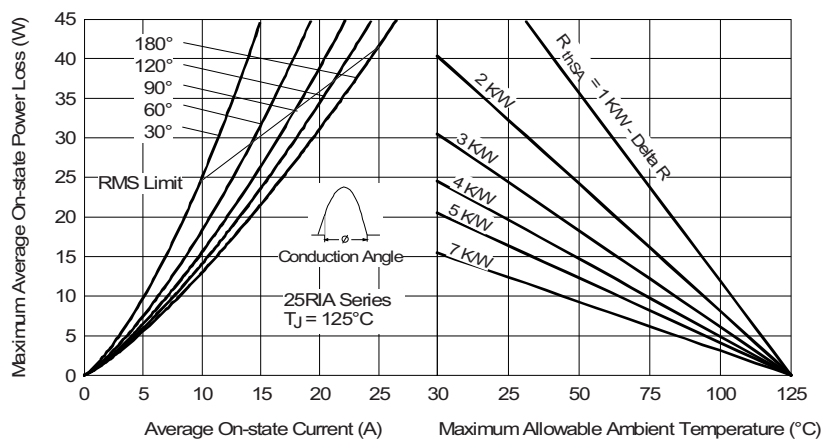


Fig. 2 - On-State Power Loss Characteristics

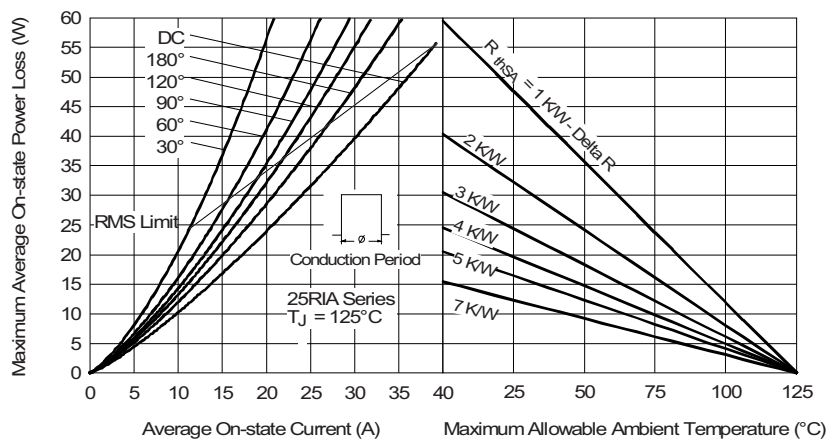


Fig. 3 - On-State Power Loss Characteristics

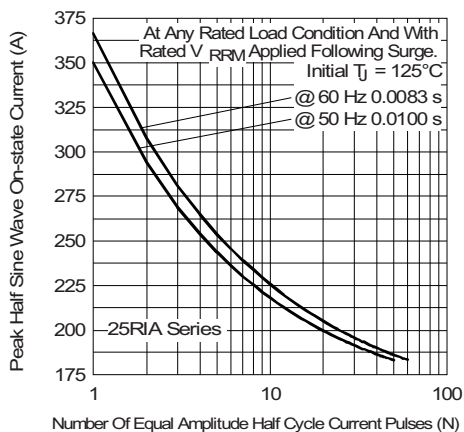


Fig. 4 - Maximum Non-Repetitive Surge Current

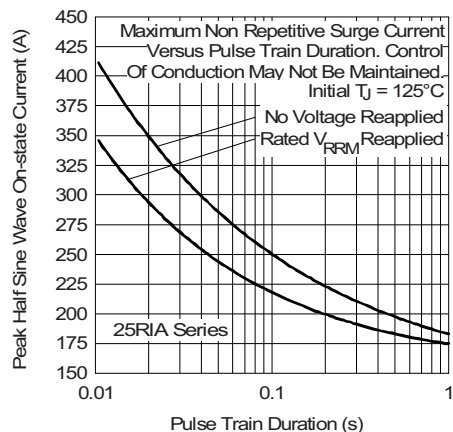


Fig. 5 - Maximum Non-Repetitive Surge Current

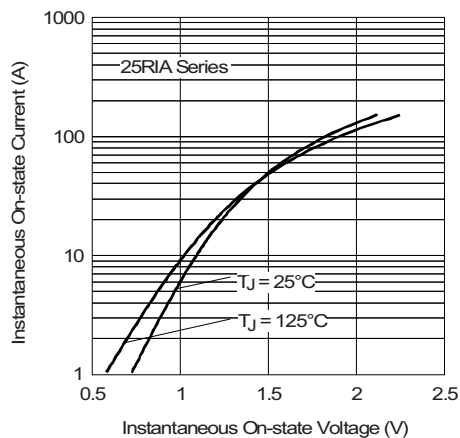


Fig. 6 - Forward Voltage Drop Characteristics

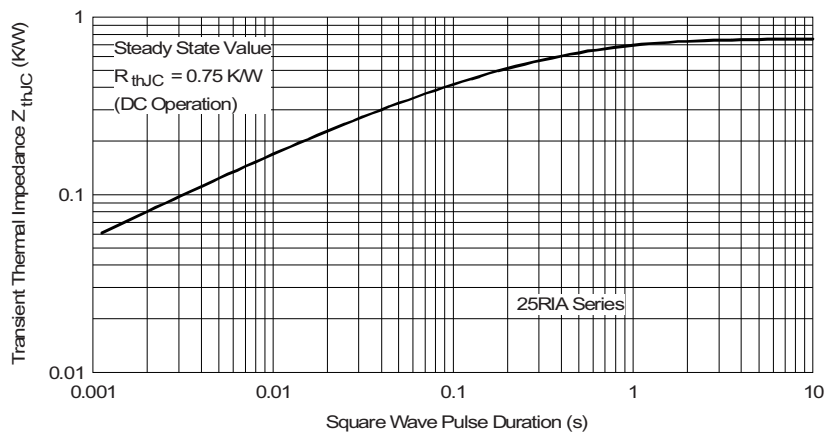


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

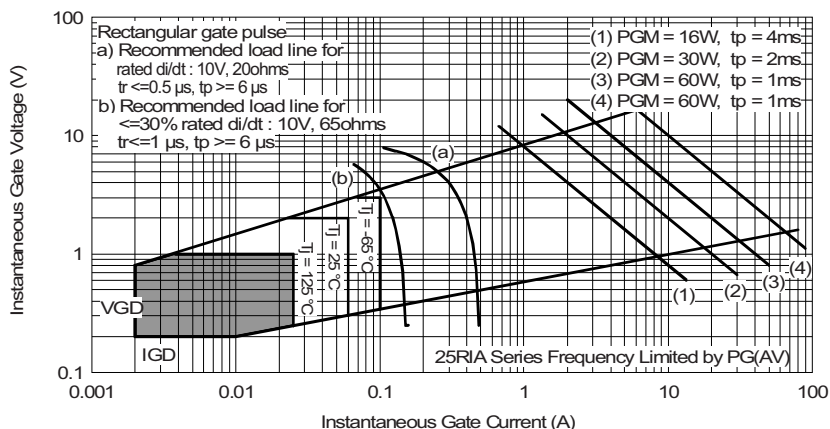


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	RIA	120	M	S90
	1	2	3	4	5	6
1	Vishay Semiconductors product					
2	Current code					
3	Essential part number					
4	Voltage code x 10 = V_{RRM} (see Voltage Ratings table)					
5	None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A M = Stud base TO-208AA (TO-48) M6 x 1					
6	Critical dV/dt : None = 300 V/ μs (standard value) S90 = 1000 V/ μs (special selection)					

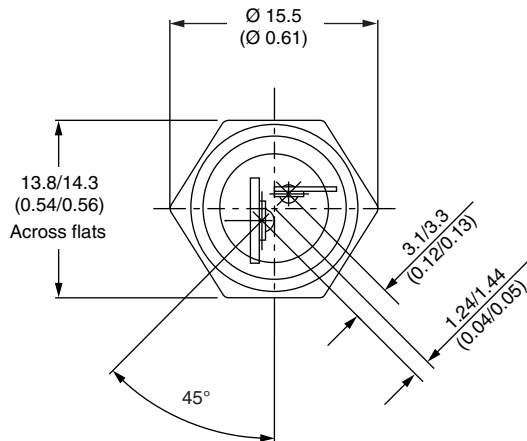
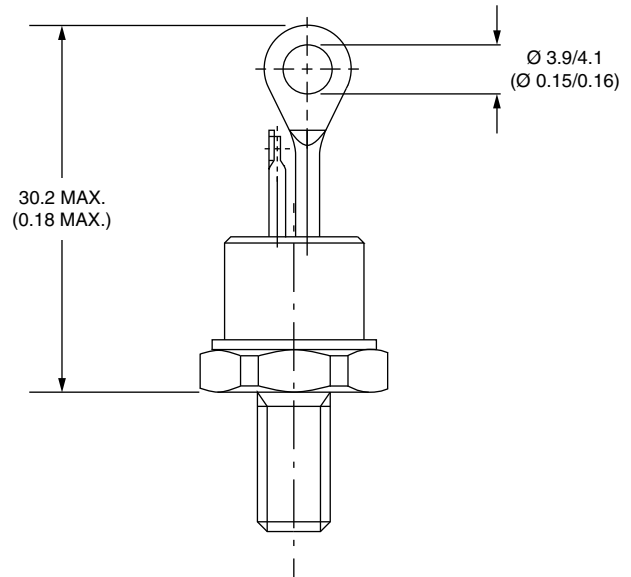
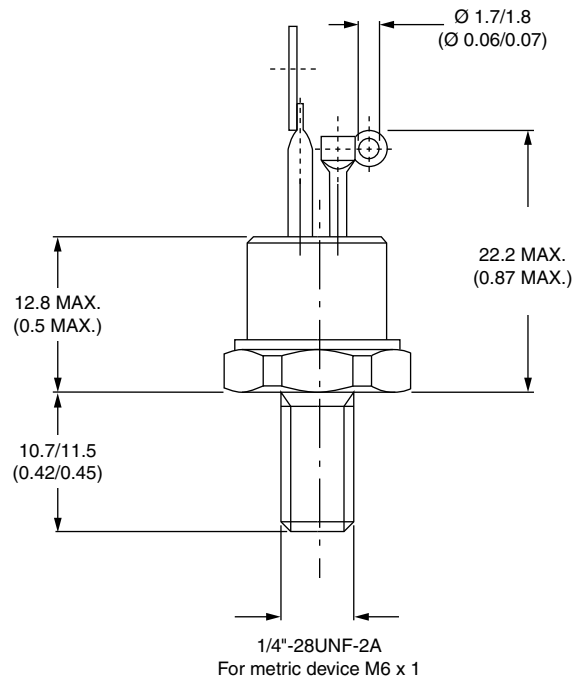
LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95333

TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)





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